

2SD789

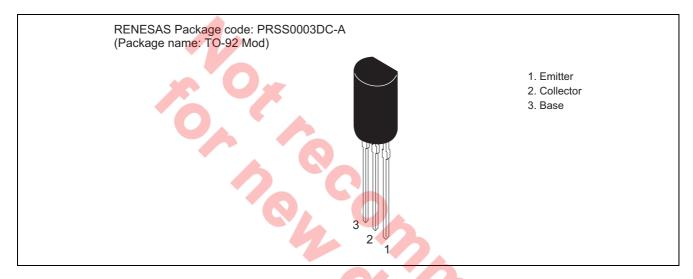
Silicon NPN Epitaxial

REJ03G0772-0300 (Previous ADE-208-1140A) Rev.3.00 Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SB740

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	V _{CBO} 100	
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	Ι _C	1	А
Collector power dissipation	Pc	0.9	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

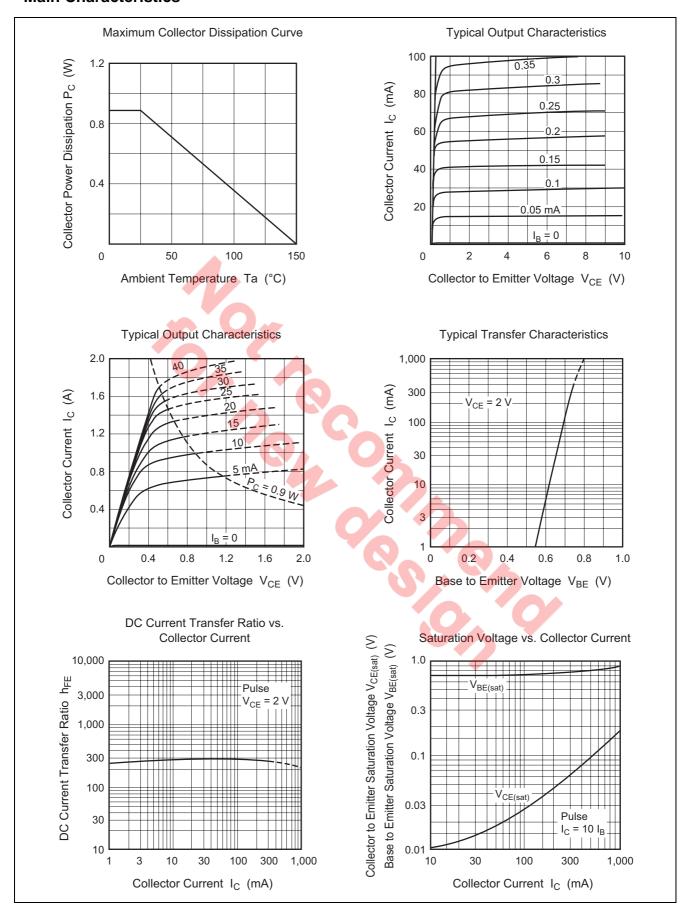
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	1	μΑ	$V_{CB} = 80 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.2	μΑ	$V_{EB} = 6 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	160	_	800		$V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	_	0.3	V	I _C = 1 A, I _B = 0.1 A
Gain bandwidth product	f⊤	_	100	_	MHz	$V_{CE} = 2 \text{ V}, I_{C} = 10 \text{ mA}$
Collector output capacitance	Cob	_	20	_	pF	V _{CB} = 10 V, I _E = 0, f = 1MHz

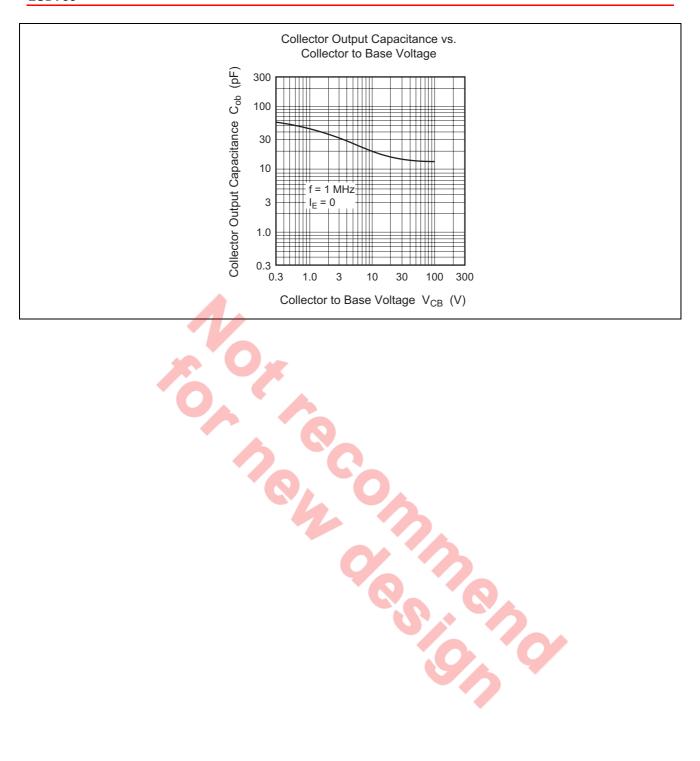
Note: 1. The 2SD789 is grouped by h_{FE} as follows.

С	D	E	
160 to 320	250 to 500	400 to 800	

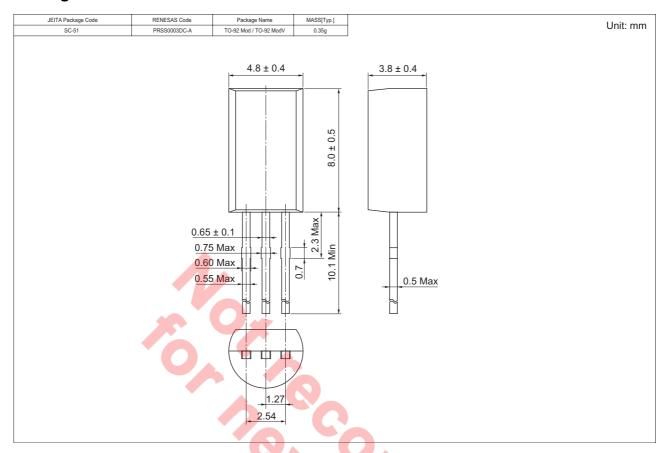


Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SD789CTZ-E	2500	Hold Box, Radial Taping
2SD789DTZ-E		
2SD789ETZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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